

## Silicon NPN Power Transistors

## 2SD1911

## DESCRIPTION

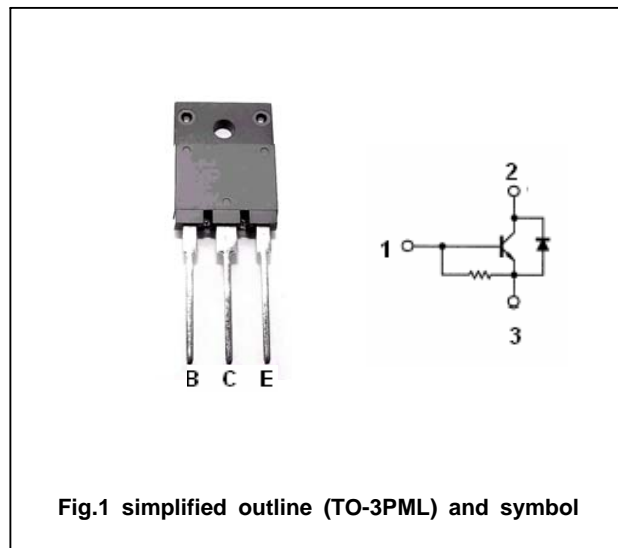
- With TO-3PML package
- High breakdown voltage
- High speed switching
- Built-in damper diode

## APPLICATIONS

- For use in TV horizontal output applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^{\circ}\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1500	V
$V_{CEO}$	Collector-emitter voltage	Open base	600	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		5	A
$I_{CM}$	Collector current-peak		10	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}\text{C}$	50	W
$T_j$	Junction temperature		150	$^{\circ}\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}\text{C}$

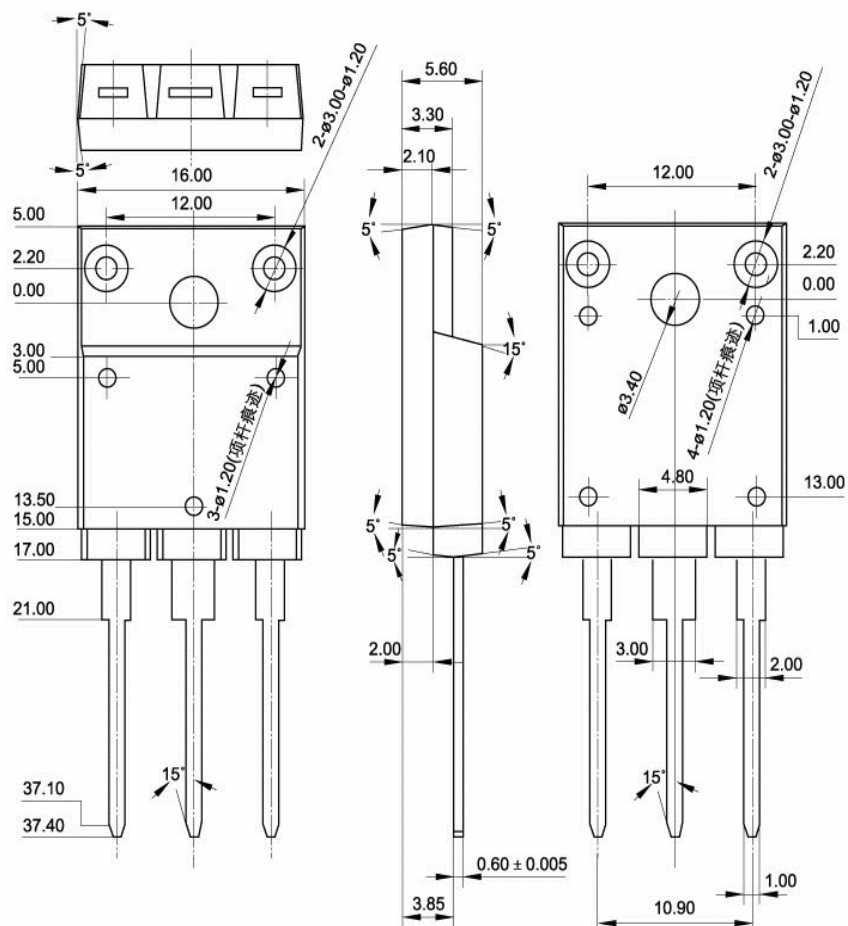
**Silicon NPN Power Transistors****2SD1911****CHARACTERISTICS****T<sub>j</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	600			V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =1.2A			5.0	V
V <sub>BE(sat)</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4.5A ; I <sub>B</sub> =1.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =800V; I <sub>E</sub> =0			10	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0	50		200	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	8		25	
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =5A			2.0	V

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## PACKAGE OUTLINE



**Fig.2 outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)**